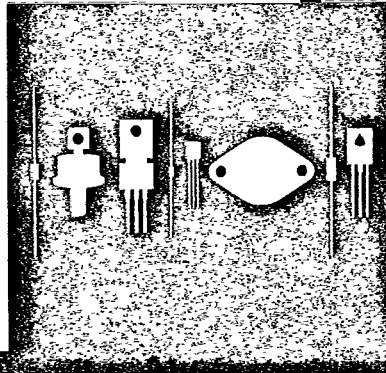


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145 Adams Avenue  
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3N246 THRU 3N252  
3N253 THRU 3N259  
SILICON BRIDGE RECTIFIERS  
CASE B

### DESCRIPTION

The CENTRAL SEMICONDUCTOR 3N246, 3N253 series types are Silicon Single Phase Full Wave Bridge Rectifiers designed for general purpose applications.

### MAXIMUM RATINGS ( $T_A=75^\circ\text{C}$ unless otherwise noted)

	3N246	3N247	3N248	3N249	3N250	3N251	3N252	
	3N253	3N254	3N255	3N256	3N257	3N258	3N259	UNIT
Peak Repetitive Reverse Voltage	$V_{RRM}$ 50	100	200	400	600	800	1000	V
DC Blocking Voltage	$V_R$ 50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_R(\text{RMS})$ 35	70	140	280	420	560	700	A
Average Forward Current (3N246 series)	$I_O$			1.0				A
Average Forward Current (3N253 series)	$I_O(55^\circ\text{C})$			2.0				A
Peak Forward Surge Current (3N246 series)	$I_{FSM}$			30				A
Peak Forward Surge Current (3N253 series)	$I_{FSM}(55^\circ\text{C})$			60				A
Operating and Storage Junction Temperature	$T_J, T_{stg}$				-65 TO +165			$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
$V_F$ (3N246 series)	$I_F=3.14\text{A}$		1.3	V
$V_F$ (3N253 series)	$I_F=3.14\text{A}$		1.1	V
$I_R$	$V_R=\text{Rated } V_{RRM}$		10	$\mu\text{A}$

# CASE OUTLINE DRAWINGS

D



CASE A

CBR1 Series  
CBR2 Series



CASE B

CBR1-L Series  
CBR2-L Series



CASE C

CBR3-P Series



CASE D

CBR4-L Series



CASE E

CBR8 Series



CASE F

CBR10 Series, CBR25 Series  
CBR12 Series, CBR30 Series

All Dimensions in Inches (Millimeters)

Drawings Not To Scale

f

